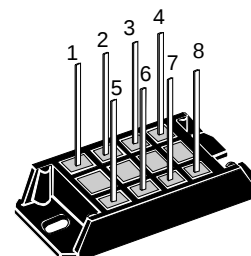
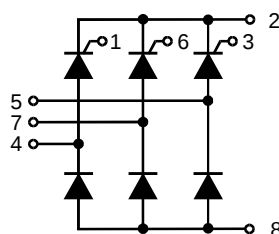


Three Phase Half Controlled Rectifier Bridge

$$\begin{aligned} I_{dAVM} &= 20 \text{ A} \\ V_{RRM} &= 1200\text{-}1600 \text{ V} \end{aligned}$$

V_{RSM}	V_{DRM}	Type
V	V	
1300	1200	VVZ 12-12io1
1500	1400	VVZ 12-14io1
1700	1600	VVZ 12-16io1



Symbol	Test Conditions		Maximum Ratings	
I_{dAV}	$T_K = 100^{\circ}\text{C}$; module module per leg		15	A
I_{dAVM}			20	A
I_{FRMS}^1, I_{TRMS}			12	A
I_{FSM}^1, I_{TSM}	$T_{VJ} = 45^{\circ}\text{C}$; $V_R = 0$	t = 10 ms (50 Hz), sine	110	A
		t = 8.3 ms (60 Hz), sine	115	A
	$T_{VJ} = T_{VJM}$ $V_R = 0$	t = 10 ms (50 Hz), sine	100	A
		t = 8.3 ms (60 Hz), sine	105	A
I^2t	$T_{VJ} = 45^{\circ}\text{C}$ $V_R = 0$	t = 10 ms (50 Hz), sine	60	A ² s
		t = 8.3 ms (60 Hz), sine	55	A ² s
	$T_{VJ} = T_{VJM}$ $V_R = 0$	t = 10 ms (50 Hz), sine	50	A ² s
		t = 8.3 ms (60 Hz), sine	45	A ² s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ f = 400 Hz, t _p = 200 μs $V_D = 2/3 V_{DRM}$ $I_G = 0.3 \text{ A}$, di _G /dt = 0.3 A/μs	repetitive, I _T = 50 A	150	A/μs
		non repetitive, I _T = 1/3 ~ I _{dAV}	500	A/μs
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)		1000	V/μs
V_{RGM}			10	V
P_{GM}	$T_{VJ} = T_{VJM}$ $I_T = I_{TAVM}$	t _p = 30 μs	≤ 10	W
		t _p = 500 μs	≤ 5	W
		t _p = 10 ms	≤ 1	W
			0.5	W
P_{GAVM}				
T_{VJ}			-40...+125	°C
T_{VJM}			125	°C
T_{stg}			-40...+125	°C
V_{ISOL}	50/60 Hz, RMS	t = 1 min	3000	V~
	$I_{ISOL} \leq 1 \text{ mA}$	t = 1 s	3600	V~
M_d	Mounting torque	(M5)	2-2.5	Nm
		(10-32 UNF)	18-22	lb.in.
Weight	typ.		28	g

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.
IXYS reserves the right to change limits, test conditions and dimensions.

Features

- Package with DCB ceramic base plate
- Isolation voltage 3600 V~
- Planar passivated chips
- Soldering terminals
- UL registered E 72873

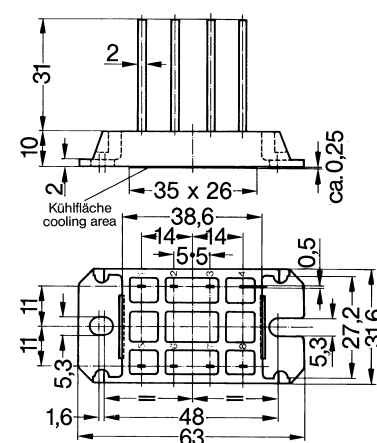
Applications

- Input rectifier for switch mode power supplies (SMPS)
- Softstart capacitor charging
- Electric drives and auxiliaries

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling

Dimensions in mm (1 mm = 0.0394")



Symbol	Test Conditions	Characteristic Values
I_R, I_D	$V_R = V_{RRM}; V_D = V_{DRM}$ $T_{VJ} = T_{VJM}$ $T_{VJ} = 25^\circ\text{C}$	$\leq 5 \text{ mA}$ $\leq 0.3 \text{ mA}$
V_F, V_T	$I_F, I_T = 30 \text{ A}, T_{VJ} = 25^\circ\text{C}$	$\leq 2 \text{ V}$
V_{T0}	For power-loss calculations only	1.1 V
r_T	$(T_{VJ} = 125^\circ\text{C})$	30 m Ω
V_{GT}	$V_D = 6 \text{ V};$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	$\leq 1.0 \text{ V}$ $\leq 1.2 \text{ V}$
I_{GT}	$V_D = 6 \text{ V};$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	$\leq 65 \text{ mA}$ $\leq 80 \text{ mA}$ $\leq 50 \text{ mA}$
V_{GD}	$T_{VJ} = T_{VJM};$ $T_{VJ} = T_{VJM};$	$V_D = 2/3 V_{DRM}$ $V_D = 2/3 V_{DRM}$
I_{GD}	$T_{VJ} = T_{VJM};$ $T_{VJ} = T_{VJM};$	$\leq 0.2 \text{ V}$ $\leq 5 \text{ mA}$
I_L	$I_G = 0.3 \text{ A}; t_G = 30 \mu\text{s}$ $di_G/dt = 0.3 \text{ A}/\mu\text{s}$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	$\leq 150 \text{ mA}$ $\leq 200 \text{ mA}$ $\leq 100 \text{ mA}$
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	$\leq 100 \text{ mA}$
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.3 \text{ A}; di_G/dt = 0.3 \text{ A}/\mu\text{s}$	$\leq 2 \mu\text{s}$
t_q	$T_{VJ} = 125^\circ\text{C}; I_T = 15 \text{ A}, t_p = 300 \mu\text{s}, -di/dt = 10 \text{ A}/\mu\text{s}$	typ. 150 μs
Q_r	$V_R = 100 \text{ V}, dv/dt = 20 \text{ V}/\mu\text{s}, V_D = 2/3 V_{DRM}$	75 μC
R_{thJC}	per thyristor (diode); DC current	2.5 K/W
	per module	0.42 K/W
R_{thJH}	per thyristor (diode); DC current	3.1 K/W
	per module	0.52 K/W
d_s	Creeping distance on surface	7 mm
d_a	Creepage distance in air	7 mm
a	Max. allowable acceleration	50 m/s ²